

Features

- $V_{RRM} = 1200\text{ V}$
- $I_{Fn} = 50\text{ A}$
- 1200 V emitter controlled technology
- Soft, fast switching
- Low reverse recovery charge
- Small temperature coefficient

Potential applications

- SMPS
- Resonant applications
- Drives

Description

Recommended for:

- Power modules
- Discrete devices



Type	Die size	Delivery form
SIDC30D120H8	5.5 mm x 5.5 mm	Sawn on foil



Table of contents

	Description	1
	Features	1
	Potential applications	1
	Table of contents	2
1	Mechanical parameters	3
2	Characteristics	4
3	Chip drawing	5
4	Bare die product specifics	6
	Revision history	7
	Disclaimer	8

SIDC30D120H8

Fast switching emitter controlled 3 diode chip

1 Mechanical parameters

1 Mechanical parameters

Table 1 Mechanical parameters

Parameter	Values
Die size	5.5 mm x 5.5 mm
Area total	30.25 mm ²
Anode pad size	See chip drawing
Silicon thickness	120 µm
Wafer size	200 mm
Maximum possible chips per wafer	878
Passivation frontside	Photoimide
Pad metal	3.2 µm AlSiCu
Backside metal	Ni Ag – system; To achieve a reliable solder connection it is strongly recommended not to consume the Ni layer completely during production process
Die attach	Electrically conductive epoxy glue and soft solder
Frontside interconnect	Wire bond: Al ≤ 500 µm
Reject ink dot size (valid for inked delivery form only)	Ø 0.65 mm; max. 1.2 mm
Storage environment (<6 months) for original and sealed MBB bags	Ambient atmosphere air, temperature 17°C – 25°C
Storage environment (<6 months) for open MBB bags	Acc. IEC 62258-3; Section 9.4 Storage Environment

2 Characteristics

Table 2 Maximum ratings

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		$T_{vj} = 25\text{ °C}$	1200	V
Continuous forward current, limited by $T_{vj,max}$ ¹⁾	I_F			-	A
Maximum repetitive forward current, tp limited by $T_{vj,max}$	I_{FRM}			100	A
Junction temperature range	T_{vj}			-40...175	°C
Operating junction temperature	T_{vjop}			-40...150	°C

1) Depending on thermal properties of assembly

Table 3 Static characteristics (tested on wafer), $T_{vj} = 25\text{ °C}$

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Diode forward voltage	V_F	$I_F = 50\text{ A}$	1.23	1.6	1.97	V
Reverse leakage current	I_R	$V_R = 1200\text{ V}$			27	μA
Cathode-anode breakdown voltage	V_{BR}	$I_R = 0.25\text{ mA}$	1200			V

Note: In general, from reliability and lifetime point of view, the lower the operation junction temperature and/or the applied voltage, the greater the expected lifetime of any semiconductor device.

For "Maximum ratings": Not subject to production test, specified by design.

3 Chip drawing

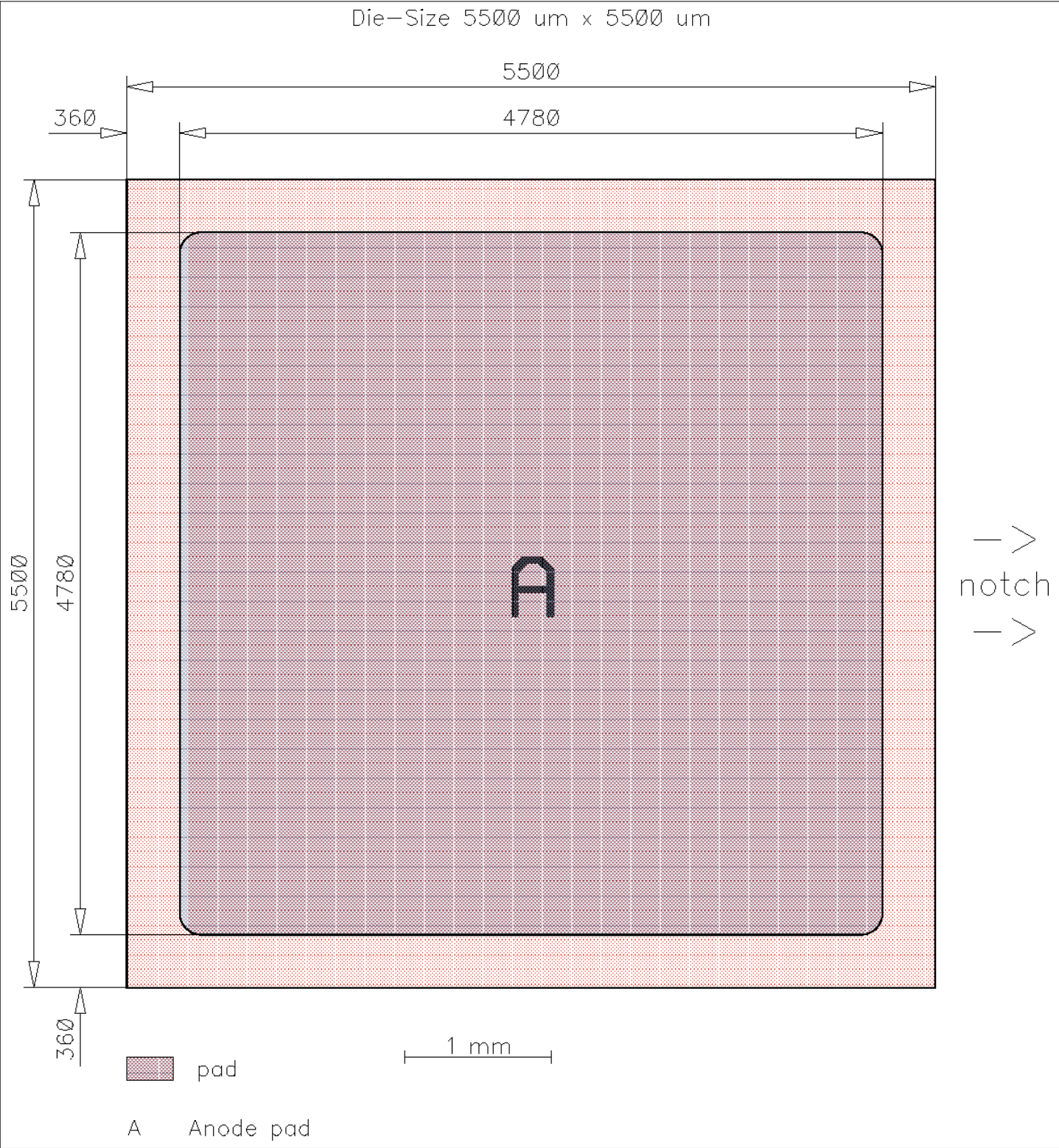


Figure 1

4 Bare die product specifics

- Switching characteristics and thermal properties are dependent on module design and mounting technology and can therefore not be specified for a bare die.
- Test coverage at wafer level cannot cover all application conditions. Therefore it is recommended to test all characteristics, which are relevant for the application at package level, including RBSOA and SCSOA.
- AQL 0.65 for visual inspection according to failure catalogue
- Electrostatic discharge sensitive device according to MIL-STD 883
- The example application may be subject to change without prior notice. It is intended for information purposes only, and should not be interpreted as a commitment.
- Example application: FS50R12KE3

SIDC30D120H8

Fast switching emitter controlled 3 diode chip

Revision history

Revision history

Document revision	Date of release	Description of changes
1.00	2022-03-23	Datasheet migrated to a new system ***Legacy Revisions*** 2.0 Final data sheet 30.12.2014 2.1 Editorial changes 14.10.2015 2.2 $I_F + I_{FRM}$ conditions changed, T_{vj} increased to 175°C, editorial changes 23.12.2021
1.10	2022-04-08	T_{vj} and T_{vjop} updated

Trademarks

All referenced product or service names and trademarks are the property of their respective owners.

Edition 2022-04-08

Published by

Infineon Technologies AG
81726 Munich, Germany

© 2022 Infineon Technologies AG
All Rights Reserved.

Do you have a question about any aspect of this document?

Email: erratum@infineon.com

Document reference
IFX-ABD244-002

IMPORTANT NOTICE

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics ("Beschaffenhheitsgarantie").

With respect to any examples, hints or any typical values stated herein and/or any information regarding the application of the product, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.

In addition, any information given in this document is subject to customer's compliance with its obligations stated in this document and any applicable legal requirements, norms and standards concerning customer's products and any use of the product of Infineon Technologies in customer's applications.

The data contained in this document is exclusively intended for technically trained staff. It is the responsibility of customer's technical departments to evaluate the suitability of the product for the intended application and the completeness of the product information given in this document with respect to such application.

Please note that this product is not qualified according to the AEC Q100 or AEC Q101 documents of the Automotive Electronics Council.

WARNINGS

Due to technical requirements products may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies office.

Except as otherwise explicitly approved by Infineon Technologies in a written document signed by authorized representatives of Infineon Technologies, Infineon Technologies' products may not be used in any applications where a failure of the product or any consequences of the use thereof can reasonably be expected to result in personal injury.